TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

SSM3K121TU

1. Applications

- Power Management Switch Applications
- High-Speed Switching Applications

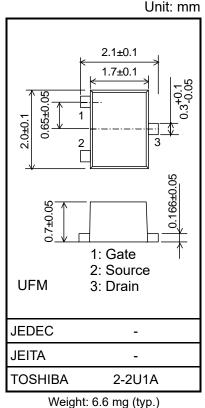
2. Features

- 1.5 V drive
- Low ON-resistance:

 $\begin{array}{l} R_{on} = 140 \ m\Omega \ (max) \ (@V_{GS} = 1.5 \ V) \\ R_{on} = \ 93 \ m\Omega \ (max) \ (@V_{GS} = 1.8 \ V) \\ R_{on} = \ 63 \ m\Omega \ (max) \ (@V_{GS} = 2.5 \ V) \\ R_{on} = \ 48 \ m\Omega \ (max) \ (@V_{GS} = 4.0 \ V) \end{array}$

3. Absolute Maximum Ratings (Ta = 25°C) (Note)

Characteristics		Symbol	Rating	Unit	
Drain-Source voltage		VDS	20	V	
Gate-Source voltage		VGSS	± 10	V	
Drain current	DC	۱ _D	3.2	A	
	Pulse	IDP	6.4		
Drain power dissipation		PD (Note 1)	800	mW	
		PD (Note 2)	500		
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	-55 to 150	°C	



Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current / voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling

Precautions" / "Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Mounted on a ceramic board.

^{(25.4} mm \times 25.4 mm \times 0.8 t, Cu Pad: 645 mm 2) Note 2: Mounted on a FR4 board.

 $^{(25.4 \}text{ mm} \times 25.4 \text{ mm} \times 1.6 \text{ t}, \text{ Cu Pad: } 645 \text{ mm}^2)$

4. Electrical Characteristics

4.1. Electrical Characteristics (Ta = 25°C)

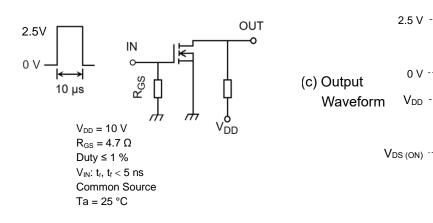
Charact	eristics	Symbol	Test Condition		Min	Тур.	Мах	Unit
Drain-Source breakdown voltage	V (BR) DSS	$I_{D} = 1 \text{ mA}, V_{GS} = 0$		20	-	-	V	
	V (BR) DSX	$I_{D} = 1 \text{ mA}, V_{GS} = -10 \text{ V}$	12	-	-			
Drain cutoff curren	t	I _{DSS}	$V_{DS} = 20 V, V_{GS} = 0$		-	-	1	μA
Gate leakage curre	ent	I _{GSS}	$V_{GS} = \pm 10 \text{ V}, \text{ V}_{DS} = 0$		-	-	±1	μA
Gate threshold vol	tage	V _{th}	$V_{DS} = 3 V, I_{D} = 1 mA$		0.35	-	1.0	V
Forward transfer a	dmittance	Y _{fs}	$V_{DS} = 3 V, I_{D} = 2.0 A$	(Note 3)	6.5	13	-	S
Drain-Source ON-resistance	R _{DS (ON)}	$I_D = 2.0 \text{ A}, V_{GS} = 4.0 \text{ V}$	(Note 3)	-	36	48	mΩ	
		$I_D = 2.0 \text{ A}, V_{GS} = 2.5 \text{ V}$	(Note 3)	-	46	63		
		$I_D = 1.0 \text{ A}, V_{GS} = 1.8 \text{ V}$	(Note 3)	-	60	93		
		$I_D = 0.5 \text{ A}, V_{GS} = 1.5 \text{ V}$	(Note 3)	-	75	140		
Input capacitance		C _{iss}			-	400	-	
Output capacitance		C _{oss}	$V_{DS} = 10 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$		-	68	-	pF
Reverse transfer of	capacitance C _{rss}			-	60	-		
Total Gate Charge	•	Qg			-	5.9	-	
Gate-Source Charge		Q _{gs}	$V_{DS} = 10 \text{ V}, \text{ I}_{DS} = 3.2 \text{ A}, \text{ V}_{GS} = 4 \text{ V}$		-	4.1	-	nC
Gate-Drain Charge		Q _{gd}			-	1.8	-	
Switching time	Turn-on time	t _{on}			-	14	-	
	Turn-off time	t _{off}		-	15	-	ns	
Drain-Source forward voltage		V _{DSF}	$I_D = -3.2 \text{ A}, V_{GS} = 0 \text{ V}$	(Note 3)	-	-0.85	-1.2	V

Note 3:Pulse test

4.2. Switching Time Test Circuit

(a) Test Circuit





90%

tf

toff

10%

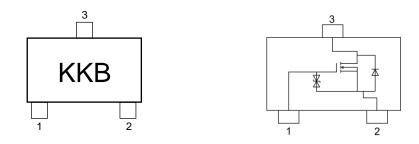
tr

ton

90%

10%

5. Marking, Equivalent Circuit (top view)



6. Notice on Usage

Vth can be expressed as the voltage between gate and source when the low operating current value is ID = 1 mA for this product. For normal switching operation, V_{GS} (on) requires a higher voltage than V_{th} , and V_{GS} (off) requires a lower voltage than V_{th} . (The relationship can be established as follows: V_{GS} (off) < V_{th} < V_{GS} (on).)

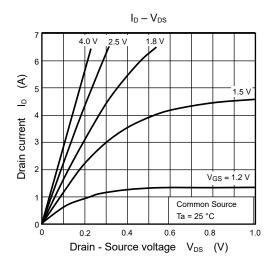
Take this into consideration when using the device.

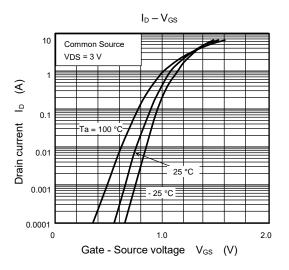
7. Handling Precaution

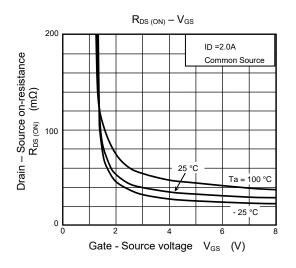
When handling individual devices that are not yet mounted on a circuit board, make sure that the environment is protected against electrostatic discharge. Operators should wear antistatic clothing, and containers and other objects that come into direct contact with devices should be made of antistatic materials.

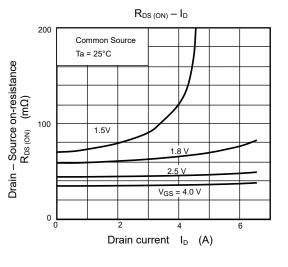
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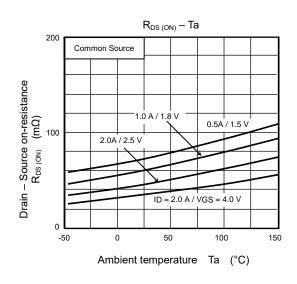
8. Characteristic Chart (Note)

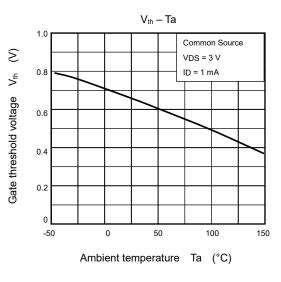




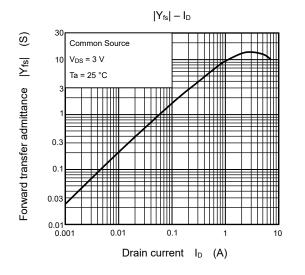


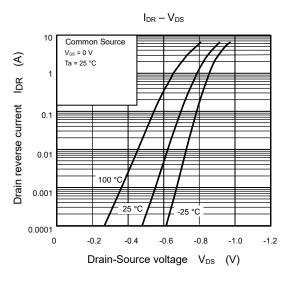




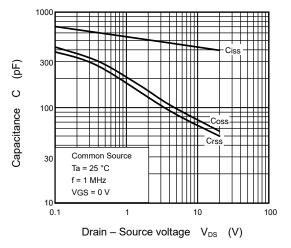


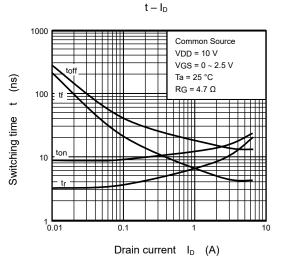
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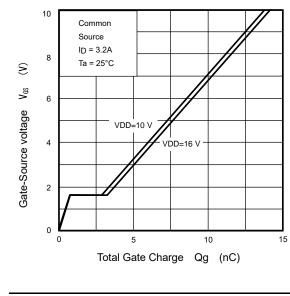




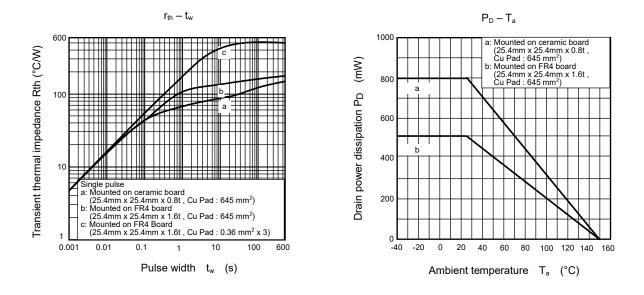
 $C-V_{\text{DS}}$







Dynamic Input Characteristic



Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

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